

7. The method of claim 4, wherein forming the plurality of metal seed material regions comprises forming aluminum regions each having a thickness in the range of 0.3 to 20 microns and comprising aluminum in an amount greater than 97% and silicon in an amount in the range of 0-2%, wherein adhering the metal foil comprises adhering an aluminum foil having a thickness in the range of 5-100 microns, and wherein isolating regions of the remaining metal foil comprises anodizing the aluminum foil by oxidizing exposed surfaces of the aluminum foil to a depth in the range of 1-20 microns.

8. The method of claim 1, wherein laser ablating through only the portion of the metal foil comprises laser ablating a thickness of the metal foil in the range of 80-99% of an entire thickness of the metal foil.

9. The method of claim 1, wherein forming the plurality of alternating N-type and P-type semiconductor regions comprises forming the alternating N-type and P-type semiconductor regions in a polycrystalline silicon layer formed above the substrate, the method further comprising:

forming a trench between each of the alternating N-type and P-type semiconductor regions, the trenches extending partially into the substrate.

10. The method of claim 1, wherein the substrate is a monocrystalline silicon substrate, and wherein forming the plurality of alternating N-type and P-type semiconductor regions comprises forming the alternating N-type and P-type semiconductor regions in the monocrystalline silicon substrate.

11. The method of claim 1, further comprising:

prior to laser ablating, forming a mask layer on at least a portion of the metal foil.

12. A method of fabricating a solar cell, the method comprising:

forming a plurality of alternating N-type and P-type semiconductor regions in or above a substrate;

adhering an anodized metal foil to the alternating N-type and P-type semiconductor regions, the anodized metal foil having an anodized top surface and an anodized bottom surface with a metal portion there between, wherein adhering the anodized metal foil to the

alternating N-type and P-type semiconductor regions comprises breaking through regions of the anodized bottom surface of the anodized metal foil; and
laser ablating through the anodized top surface and the metal portion of the anodized metal foil at regions corresponding to locations between the alternating N-type and P-type semiconductor regions, wherein the laser ablating terminates at the anodized bottom surface of the anodized metal foil isolating regions of the remaining metal foil corresponding to the alternating N-type and P-type semiconductor regions.

13. The method of claim 12, further comprising:

prior to adhering the anodized metal foil, forming a plurality of metal seed material regions to provide a metal seed material region on each of the alternating N-type and P-type semiconductor regions, wherein adhering the anodized metal foil to the alternating N-type and P-type semiconductor regions comprises adhering the anodized metal foil the plurality of metal seed material regions.

14. The method of claim 13, further comprising:

prior to adhering the anodized metal foil to the plurality of metal seed material regions, forming an insulating layer on the plurality of metal seed material regions, wherein adhering the anodized metal foil to the plurality of metal seed material regions comprises breaking through regions of the insulating layer.

15. The method of claim 13, wherein adhering the anodized metal foil to the plurality of metal seed material regions comprises using a technique selected from the group consisting of a laser welding process, a thermal compression process and an ultrasonic bonding process.

16. The method of claim 13, wherein forming the plurality of metal seed material regions comprises forming aluminum regions each having a thickness in the range of 0.3 to 20 microns and comprising aluminum in an amount greater than 97% and silicon in an amount in the range of 0-2%, wherein adhering the anodized metal foil comprises adhering an anodized aluminum foil having a total thickness in the range of 5-100 microns with the anodized top surface and anodized bottom surface each contributing a thickness in the range of 1-20 microns.